MAIL ROOM
JUN 5 1995
PAT. & TM OFFICE

Form PTO-1449
(Rev. 8-83)

U.S. Department of Commerce
Patent and Trademark Office

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Atty.Docket No. 0756-1299	Serial No. (TO BE ASSIGNED) Based on S.N. 08/~~248,220~~ 811742
Applicant Hongyong ZHANG et al.	
Filing Date June 5, 1995	Group 2508

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
LR		5,147,826	09/15/92	Liu et al.	437	233	
LR		5,275,851	01/04/94	Fonash et al.	437	233	
LR		4,746,628	5/24/88	Takafuji et al.	257	352	

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
LR		2-208635	8/90	Japan	Iwamatsu	257	57	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

LR — C. Hayzelden et al., "*In Situ* Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon" ~~(2 pages)~~ Appl. Phys. Lett. 60, 2 (1992) 225

LR — A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", ~~Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR, pp. 635-640.~~ Phys. Stat. Sol. 495 (1986) 635

LR — T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", Solid State Communications, Vol. 85, No. 11, pp. 921-924, 1993.

Examiner L RADOMSKY — Date Considered 10/4/95

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.